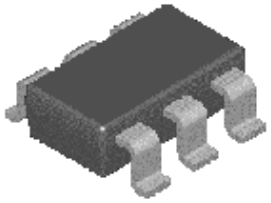
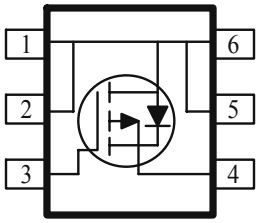
# P-Channel 60-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (±25) for battery pack applications

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | $r_{DS(on)}$ (Ω) | $I_D$ (A) |
| -60 | 0.310 @ $V_{GS}$ = -10V | 2.1 |
| | 0.465 @ $V_{GS}$ = -4.5V | 1.7 |






| ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25 °C UNLESS OTHERWISE NOTED) | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Maximum** | **Units** |
| Drain-Source Voltage | | $V_{DS}$ | -60 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | |
| Continuous Drain Current[a] | $T_A$=25°C | $I_D$ | 2.1 | A |
| | $T_A$=70°C | | 1.7 | |
| Pulsed Drain Current[b] | | $I_{DM}$ | ±15 | |
| Continuous Source Current (Diode Conduction)[a] | | $I_S$ | -1.7 | A |
| Power Dissipation[a] | $T_A$=25°C | $P_D$ | 2.0 | W |
| | $T_A$=70°C | | 1.3 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | -55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **Parameter** | | **Symbol** | **Maximum** | **Units** |
| Maximum Junction-to-Ambient[a] | t <= 5 sec | $R_{\theta JA}$ | 62.5 | °C/W |
| | | | 110 | °C/W |

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

| SPECIFICATIONS ($T_A$ = 25°C UNLESS OTHERWISE NOTED) | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Limits** | | | **Unit** |
| | | | **Min** | **Typ** | **Max** | |
| **Static** | | | | | | |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = -250 uA | -1 | | | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = -48 V, $V_{GS}$ = 0 V | | | -1 | uA |
| | | $V_{DS}$ = -48 V, $V_{GS}$ = 0 V, $T_J$ = 55°C | | | -10 | |
| On-State Drain Current[A] | $I_{D(on)}$ | $V_{DS}$ = -5 V, $V_{GS}$ = -10 V | -20 | | | A |
| Drain-Source On-Resistance[A] | $r_{DS(on)}$ | $V_{GS}$ = -10 V, $I_D$ = -2.1 A | | | 310 | mΩ |
| | | $V_{GS}$ = -4.5 V, $I_D$ = -1.7 A | | | 465 | |
| Forward Tranconductance[A] | $g_{fs}$ | $V_{DS}$ = -15 V, $I_D$ = -2.1 A | | 8 | | S |
| Diode Forward Voltage | $V_{SD}$ | $I_S$ = -2.5 A, $V_{GS}$ = 0 V | | | -1.2 | V |
| **Dynamic[b]** | | | | | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = -30 V, $V_{GS}$ = -4.5 V, $I_D$ = -2.1 A | | 18 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 5 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 2 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = -30 V, $R_L$ = 30 Ω , ID = -1 A, VGEN = -10 V, RG = 6Ω | | 8 | | nS |
| Rise Time | $t_r$ | | | 10 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 35 | | |
| Fall-Time | $t_f$ | | | 12 | | |

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.